

REMARKS

Reconsideration and further examination of the present application is respectfully requested.

Objection to the Drawings

In paragraph 1 on page 2 of the Office Action, the drawings are objected to because "Figure 1 should be designated by a legend such as --Prior Art-- because only that which is old is illustrated."

Applicant respectfully submits herewith under separate cover proposed drawing corrections in red for original Figure 1.

Applicant respectfully submits this objection has been overcome and should accordingly be withdrawn.

Rejections Under 35 U.S.C. §§ 102(e), 103(a)

In paragraph 2 on pages 2-8 of the Office Action, claims 25-36, 38-55, and 57-60 are rejected under 35 U.S.C. § 102(e) as being anticipated by U.S. Patent No. 6,037,232 to Wieczorek et al. ("Wieczorek").

In paragraph 3 on page 8 of the Office Action, claims 37 and 56 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Wieczorek and U.S. Patent No. 5,880,500 to Iwata et al. ("Iwata").

Applicant respectfully traverses these rejections as follows.

Applicant respectfully submits neither Wieczorek nor Iwata, whether alone or in any combination with one another, taught or suggested a source/drain terminal comprising an implanted region, a first silicide layer in the implanted region, and a second silicide layer in the implanted region as claimed in independent claim 25.

Applicant also respectfully submits neither Wieczorek nor Iwata, whether alone or in any combination with one another, taught or suggested a source/drain terminal comprising a first implanted region, a first silicide layer in the first implanted region, a second implanted region, and a second silicide layer in the second implanted region as claimed in independent claim 42.

Applicant respectfully submits only one of the two silicide layers 219B of Wieczorek is in an implanted region. See, e.g., Fig. 2D.

Noting claims 26-41 and 43-60 depend from claim 25 or 42, Applicant respectfully submits these rejections have been overcome and should accordingly be withdrawn.

VERSION WITH MARKINGS TO SHOW CHANGES MADE

25. (Amended Once) A microelectronic structure comprising:
- a gate electrode; and
 - a source/drain terminal aligned with the gate electrode, the source/drain terminal comprising an implanted region, a first silicide layer in the implanted region, and a second silicide layer in the implanted region.
42. (Amended Once) A microelectronic structure comprising:
- a gate electrode; and
 - a source/drain terminal aligned with the gate electrode, the source/drain terminal comprising a first implanted region, a first silicide layer in the first implanted region, a second implanted region, and a second silicide layer in the second implanted region.

In view of the foregoing remarks, it is respectfully submitted the present application is in condition for allowance, for which early action is earnestly solicited.

The Examiner is invited to telephone the undersigned to help expedite any further prosecution of the present application.

The Director of the U.S. Patent and Trademark Office is hereby authorized to credit any overpayment or to charge any fees or fee deficiencies under 37 C.F.R. §§ 1.16 and 1.17 in connection with this communication to our Deposit Account No. 02-2666.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR
& ZAFMAN, L.L.P.

A handwritten signature in black ink, appearing to read "Matthew C. Fagan", with a large, stylized flourish at the end.

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